

Schottky Barrier Diode

RB715F / RB715W

●Applications

General purpose detection
High speed switching

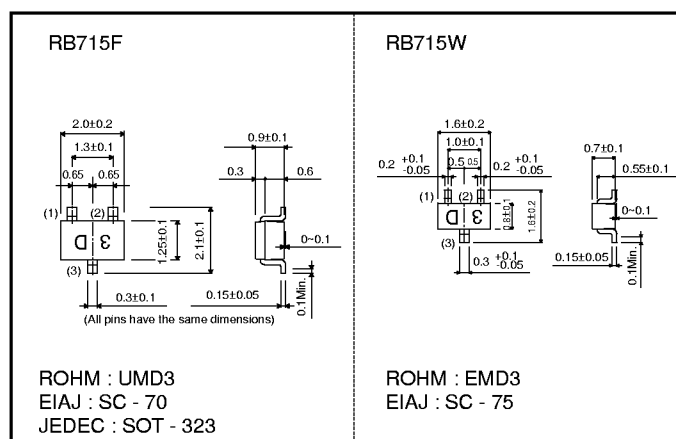
●Features

- 1) Designed for mounting on small surface areas
- 2) High reliability
- 3) Low V_F / low I_R

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.28	0.37	V	$I_F=1\text{mA}$
Reverse current	I_R	-	0.05	1	μA	$V_R=10\text{V}$
Capacitance between terminals	C_T	-	2.0	-	pF	$V_R=1\text{V}$, $f=1\text{MHz}$

* ESD sensitive product handling required.

Diodes

● Electrical characteristic curves ($T_a=25^\circ\text{C}$)